

MC14069UB

Hex Inverter

The MC14069UB hex inverter is constructed with MOS P-channel and N-channel enhancement mode devices in a single monolithic structure. These inverters find primary use where low power dissipation and/or high noise immunity is desired. Each of the six inverters is a single stage to minimize propagation delays.

- Supply Voltage Range = 3.0 Vdc to 18 Vdc
- Capable of Driving Two Low-Power TTL Loads or One Low-Power Schottky TTL Load Over the Rated Temperature Range
- Triple Diode Protection on All Inputs
- Pin-for-Pin Replacement for CD4069UB
- Meets JEDEC UB Specifications

MAXIMUM RATINGS (Voltages Referenced to V_{SS}) (Note 2.)

Symbol	Parameter	Value	Unit
V_{DD}	DC Supply Voltage Range	-0.5 to +18.0	V
V_{in}, V_{out}	Input or Output Voltage Range (DC or Transient)	-0.5 to $V_{DD} + 0.5$	V
I_{in}, I_{out}	Input or Output Current (DC or Transient) per Pin	± 10	mA
P_D	Power Dissipation, per Package (Note 3.)	500	mW
T_A	Ambient Temperature Range	-55 to +125	°C
T_{stg}	Storage Temperature Range	-65 to +150	°C
T_L	Lead Temperature (8-Second Soldering)	260	°C

2. Maximum Ratings are those values beyond which damage to the device may occur.

3. Temperature Derating:

Plastic "P and D/DW" Packages: - 7.0 mW/°C From 65°C To 125°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range $V_{SS} \leq (V_{in} \text{ or } V_{out}) \leq V_{DD}$.

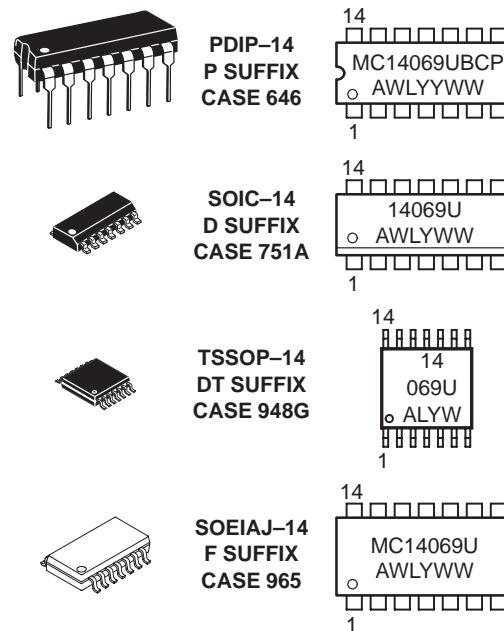
Unused inputs must always be tied to an appropriate logic voltage level (e.g., either V_{SS} or V_{DD}). Unused outputs must be left open.



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MARKING DIAGRAMS



A = Assembly Location

WL or L = Wafer Lot

YY or Y = Year

WW or W = Work Week

ORDERING INFORMATION

Device	Package	Shipping
MC14069UBCP	PDIP-14	2000/Box
MC14069UBD	SOIC-14	2750/Box
MC14069UBDR2	SOIC-14	2500/Tape & Reel
MC14069UBDT	TSSOP-14	96/Rail
MC14069UBTEL	TSSOP-14	2000/Tape & Reel
MC14069UBDTR2	TSSOP-14	2500/Tape & Reel
MC14069UBF	SOEIAJ-14	See Note 1.
MC14069UBFEL	SOEIAJ-14	See Note 1.

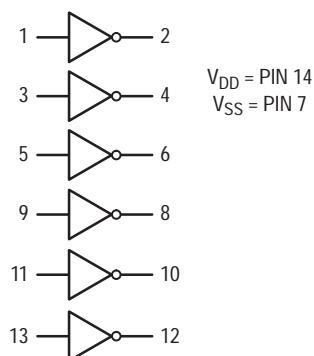
1. For ordering information on the EIAJ version of the SOIC packages, please contact your local ON Semiconductor representative.

MC14069UB

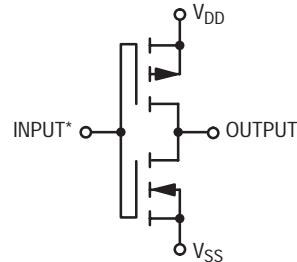
PIN ASSIGNMENT

IN 1	1	14	V _{DD}
OUT 1	2	13	IN 6
IN 2	3	12	OUT 6
OUT 2	4	11	IN 5
IN 3	5	10	OUT 5
OUT 3	6	9	IN 4
V _{SS}	7	8	OUT 4

LOGIC DIAGRAM



CIRCUIT SCHEMATIC (1/6 OF CIRCUIT SHOWN)



*Double diode protection on all inputs not shown.

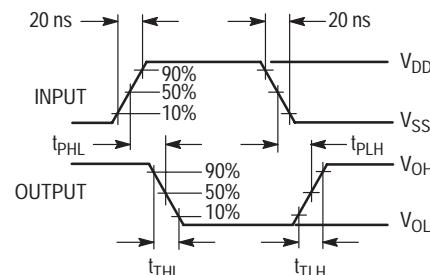
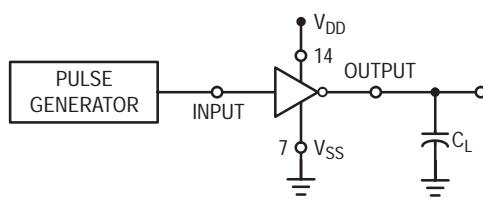


Figure 1. Switching Time Test Circuit and Waveforms

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ELECTRICAL CHARACTERISTICS (Voltages Referenced to V_{SS})

Characteristic	Symbol	V _{DD} Vdc	-55°C		25°C			125°C		Unit
			Min	Max	Min	Typ (4.)	Max	Min	Max	
Output Voltage V _{in} = V _{DD}	V _{OL}	5.0	—	0.05	—	0	0.05	—	0.05	Vdc
		10	—	0.05	—	0	0.05	—	0.05	
		15	—	0.05	—	0	0.05	—	0.05	
	V _{OH}	5.0	4.95	—	4.95	5.0	—	4.95	—	Vdc
		10	9.95	—	9.95	10	—	9.95	—	
		15	14.95	—	14.95	15	—	14.95	—	
Input Voltage (V _O = 4.5 Vdc) (V _O = 9.0 Vdc) (V _O = 13.5 Vdc)	V _{IL}	5.0	—	1.0	—	2.25	1.0	—	1.0	Vdc
		10	—	2.0	—	4.50	2.0	—	2.0	
		15	—	2.5	—	6.75	2.5	—	2.5	
	V _{IH}	5.0	4.0	—	4.0	2.75	—	4.0	—	Vdc
		10	8.0	—	8.0	5.50	—	8.0	—	
		15	12.5	—	12.5	8.25	—	12.5	—	
Output Drive Current (V _{OH} = 2.5 Vdc) (V _{OH} = 4.6 Vdc) (V _{OH} = 9.5 Vdc) (V _{OH} = 13.5 Vdc)	Source	I _{OH}	5.0	-3.0	—	-2.4	-4.2	—	-1.7	mA
			5.0	-0.64	—	-0.51	-0.88	—	-0.36	
			10	-1.6	—	-1.3	-2.25	—	-0.9	
			15	-4.2	—	-3.4	-8.8	—	-2.4	
	Sink	I _{OL}	5.0	0.64	—	0.51	0.88	—	0.36	mA
			10	1.6	—	1.3	2.25	—	0.9	
			15	4.2	—	3.4	8.8	—	2.4	
Input Current	I _{in}	15	—	±0.1	—	±0.00001	±0.1	—	±1.0	μA
Input Capacitance (V _{in} = 0)	C _{in}	—	—	—	—	5.0	7.5	—	—	pF
Quiescent Current (Per Package)	I _{DD}	5.0	—	0.25	—	0.0005	0.25	—	7.5	μA
Total Supply Current (5.) (6.) (Dynamic plus Quiescent, Per Gate) (C _L = 50 pF)	I _T	5.0	I _T = (0.3 μA/kHz) f + I _{DD} /6 I _T = (0.6 μA/kHz) f + I _{DD} /6 I _T = (0.9 μA/kHz) f + I _{DD} /6						μA	
	t _{TLH} , t _{THL}	10								
		15								
		5.0	—	—	—	100	200	—	—	ns
Output Rise and Fall Times (5.) (C _L = 50 pF) t _{TLH} , t _{THL} = (1.35 ns/pF) C _L + 33 ns t _{TLH} , t _{THL} = (0.60 ns/pF) C _L + 20 ns t _{TLH} , t _{THL} = (0.40 ns/pF) C _L + 20 ns	t _{PLH} , t _{PHL}	10	—	—	—	50	100	—	—	ns
		15	—	—	—	40	80	—	—	
		5.0	—	—	—	65	125	—	—	
		10	—	—	—	40	75	—	—	
		15	—	—	—	30	55	—	—	
Propagation Delay Times (5.) (C _L = 50 pF) t _{PLH} , t _{PHL} = (0.90 ns/pF) C _L + 20 ns t _{PLH} , t _{PHL} = (0.36 ns/pF) C _L + 22 ns t _{PLH} , t _{PHL} = (0.26 ns/pF) C _L + 17 ns	t _{PLH} , t _{PHL}	5.0	—	—	—	—	—	—	—	ns
		10	—	—	—	—	—	—	—	
		15	—	—	—	—	—	—	—	
		5.0	—	—	—	—	—	—	—	
		10	—	—	—	—	—	—	—	

4. Data labelled "Typ" is not to be used for design purposes but is intended as an indication of the IC's potential performance.

5. The formulas given are for the typical characteristics only at 25°C.

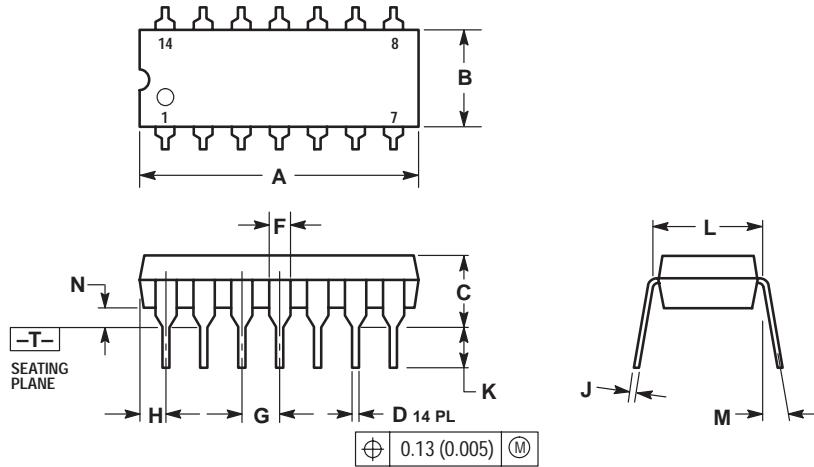
6. To calculate total supply current at loads other than 50 pF:

$$I_T(C_L) = I_T(50 \text{ pF}) + (C_L - 50) Vfk$$

where: I_T is in μA (per package), C_L in pF, V = (V_{DD} - V_{SS}) in volts, f in kHz is input frequency, and k = 0.002.

PACKAGE DIMENSIONS

P SUFFIX
PLASTIC DIP PACKAGE
CASE 646-06
ISSUE M



NOTES:

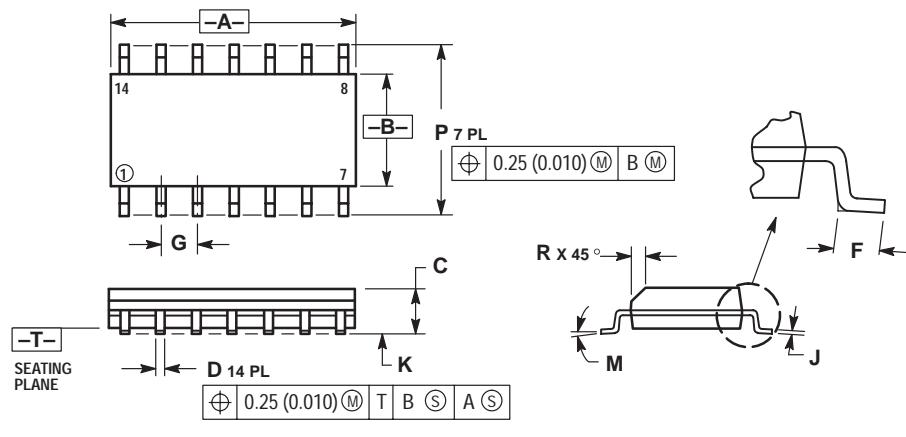
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSION L TO CENTER OF LEADS WHEN FORMED PARALLEL.
4. DIMENSION B DOES NOT INCLUDE MOLD FLASH.
5. ROUNDED CORNERS OPTIONAL.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.715	0.770	18.16	18.80
B	0.240	0.260	6.10	6.60
C	0.145	0.185	3.69	4.69
D	0.015	0.021	0.38	0.53
F	0.040	0.070	1.02	1.78
G	0.100 BSC		2.54 BSC	
H	0.052	0.095	1.32	2.41
J	0.008	0.015	0.20	0.38
K	0.115	0.135	2.92	3.43
L	0.290	0.310	7.37	7.87
M	—	10°	—	10°
N	0.015	0.039	0.38	1.01

MC14069UB

PACKAGE DIMENSIONS

D SUFFIX
PLASTIC SOIC PACKAGE
CASE 751A-03
ISSUE F



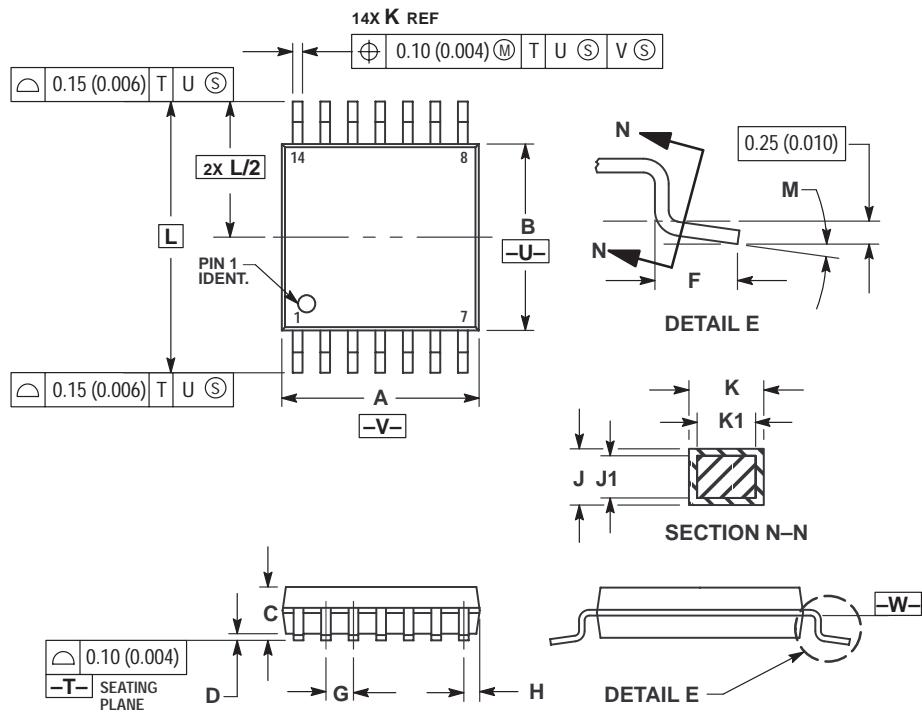
NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	8.55	8.75	0.337	0.344
B	3.80	4.00	0.150	0.157
C	1.35	1.75	0.054	0.068
D	0.35	0.49	0.014	0.019
F	0.40	1.25	0.016	0.049
G	1.27 BSC		0.050 BSC	
J	0.19	0.25	0.008	0.009
K	0.10	0.25	0.004	0.009
M	0 °	7 °	0 °	7 °
P	5.80	6.20	0.228	0.244
R	0.25	0.50	0.010	0.019

PACKAGE DIMENSIONS

DT SUFFIX
PLASTIC TSSOP PACKAGE
CASE 948G-01
ISSUE O



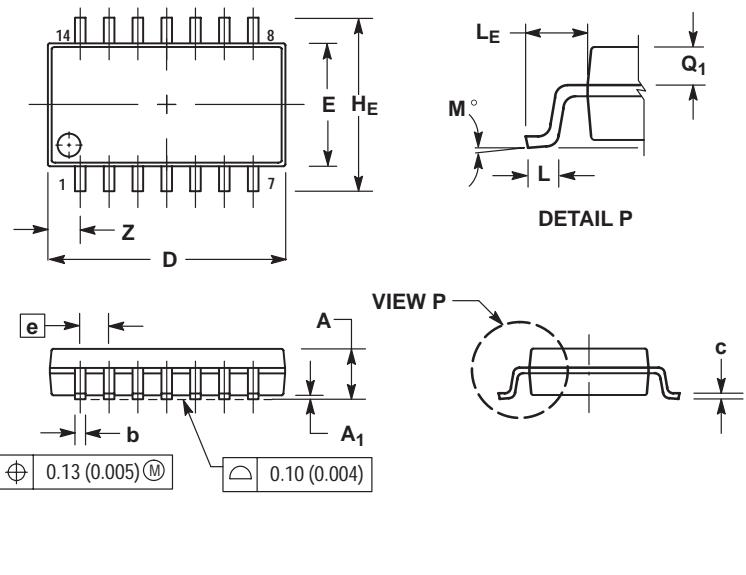
NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.90	5.10	0.193	0.200
B	4.30	4.50	0.169	0.177
C	—	1.20	—	0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC	—	0.026 BSC	—
H	0.50	0.60	0.020	0.024
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40 BSC	—	0.252 BSC	—
M	0°	8°	0°	8°

PACKAGE DIMENSIONS

F SUFFIX
PLASTIC EIAJ SOIC PACKAGE
CASE 965-01
ISSUE O



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS AND ARE MEASURED AT THE PARTING LINE. MOLD FLASH OR PROTRUSIONS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
4. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
5. THE LEAD WIDTH DIMENSION (b) DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE LEAD WIDTH DIMENSION AT MAXIMUM MATERIAL CONDITION. DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OR THE FOOT. MINIMUM SPACE BETWEEN PROTRUSIONS AND ADJACENT LEAD TO BE 0.46 (0.018).

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	---	2.05	---	0.081
A ₁	0.05	0.20	0.002	0.008
b	0.35	0.50	0.014	0.020
c	0.18	0.27	0.007	0.011
D	9.90	10.50	0.390	0.413
E	5.10	5.45	0.201	0.215
e	1.27 BSC		0.050 BSC	
H _E	7.40	8.20	0.291	0.323
Q ₁	0.50	0.85	0.020	0.033
L _E	1.10	1.50	0.043	0.059
M	0 °	10 °	0 °	10 °
Z	---	1.42	---	0.056

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